AMENDMENTS TO THE CLAIMS:

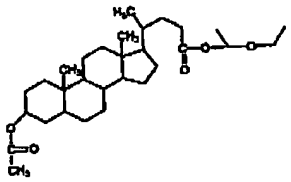
Please amend the claims as follows:

Claims 1-12 (Canceled)

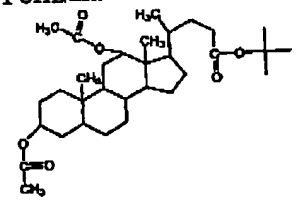
13. (Currently Amended) A resist flow process for forming a photoresist pattern comprising the steps of:

(a) forming a first photoresist pattern on a substrate using a photoresist composition comprising a photoresist polymer, a photo acid generator, an organic solvent, and an additive selected from the group consisting of compounds of the following Formulas 3 to 7:

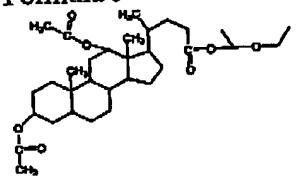
Formula 3



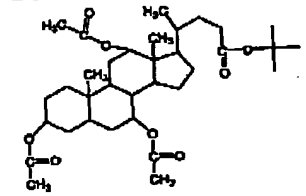
Formula 4



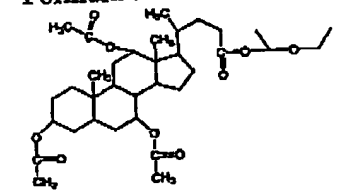
Formula 5



Formula 6



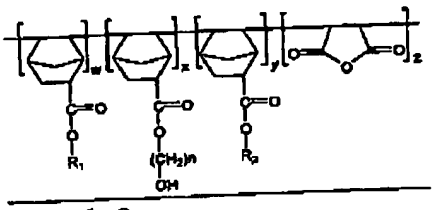
Formula 7



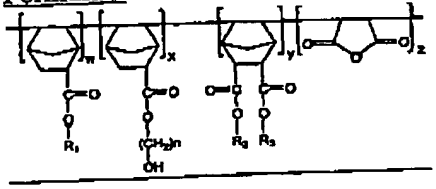
~~and~~

wherein said photoresist polymer is a compound selected from the group consisting of the following Formulas 8 and 9:

Formula 8



Formula 9



wherein, R_1 is an acid labile protecting group;

R_2 is hydrogen; R_3 is selected from the group consisting of hydrogen, C_1-C_{10} alkyl, C_1-C_{10} alkoxyalkyl, and C_1-C_{10} alkyl containing at least one hydroxyl group (-OH);

n is an integer from 1 to 5; and w + x + y = 50mol%, and z is 50mol%; and

(b) performing resist flow process onto the first photoresist pattern to obtain a second photoresist pattern.

14. (Previously Presented) The resist flow process according to claim 13, wherein said step (a) further comprises the steps of:

(i) coating said photoresist composition on said substrate to form a photoresist film, wherein said substrate is a semiconductor devise; and

(ii) producing said first photoresist pattern using a lithography process.

15. (Previously Presented) The resist flow process according to claim 13, wherein said first and second photoresist pattern comprises a contact hole pattern.

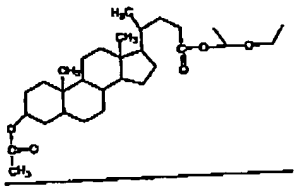
16. (Currently Amended) The resist flow process according to claim 13, wherein said resist flow process comprises heating ~~said first photoresist pattern up to Tg~~ to a temperature between Tg of ~~the~~ photoresist polymer and a decomposition temperature (T_d) where the polymer starts to be decomposed.

Clams 17-22 (Canceled)

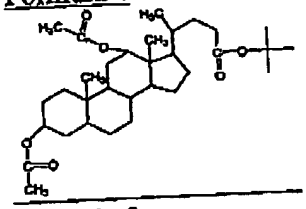
23. (Currently Amended) ~~The~~ A resist flow process ~~according to claim 13~~ for forming a photoresist pattern comprising the steps of:

(a) forming a first photoresist pattern on a substrate using a photoresist composition comprising a photoresist polymer, a photo acid generator, an organic solvent, and an additive selected from the group consisting of compounds of following Formulas 3 to 7:

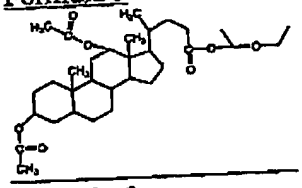
Formula 3



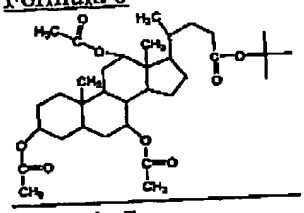
Formula 4



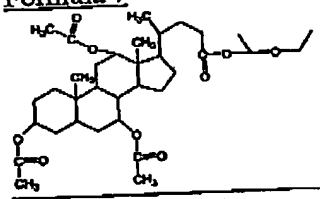
Formula 5



Formula 6



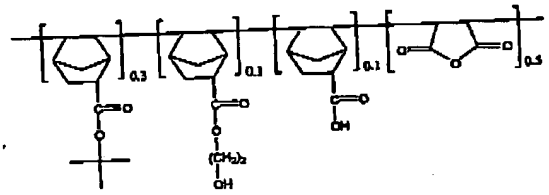
Formula 7



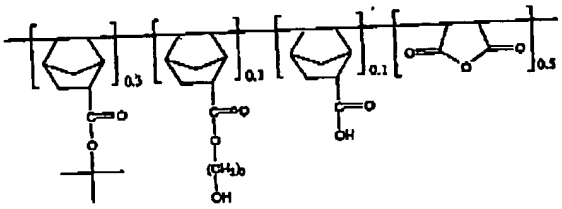
and

(b) performing a resist flow process onto the first photoresist pattern to obtain a second photoresist pattern, wherein said photoresist polymer is selected from the group consisting of ~~at least one of~~ the following Formulas 10 to 13:

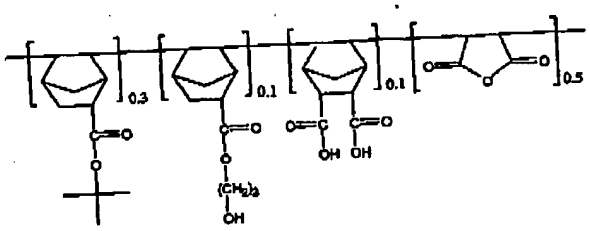
Formula 10



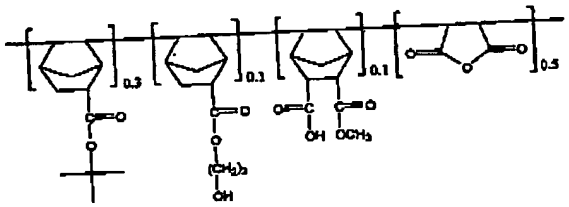
Formula 11



Formula 12



Formula 13



24. (Currently Amended) The resist flow process according to claim 13, wherein said additive is present in an amount ranging from 1wt% to 70wt% ~~by weight~~ of the photoresist polymer.

25. (Previously Presented) The resist flow process according to claim 13, wherein said photoacid generator is selected from the group consisting of diphenyl iodide hexafluorophosphate, diphenyl iodide hexafluoroarsenate, diphenyl iodide hexafluoroantimonate, diphenyl p-methoxyphenyl triflate, diphenyl p-toluenyl triflate, diphenyl p-isobutylphenyl triflate, diphenyl p-tert-butylphenyl triflate, triphenylsulfonium hexafluororphosphate, triphenylsulfonium hexafluoroarsenate, triphenylsulfonium hexafluoroantimonate, triphenylsulfonium triflate, dibutylnaphthylsulfonium triflate, and mixtures thereof .

26. (Currently Amended) The resist flow process according to claim 13, wherein said photoacid generator is present in an amount ranging from 0.01wt% to 10wt% ~~by weight~~ of the photoresist polymer.

27. (Previously Presented) The resist flow process according to claim 13, wherein said organic solvent is selected from the group consisting of propyleneglycol methyl

ether acetate, ethyl lactate, methyl 3-methoxypropionate, ethyl 3-ethoxypropionate and cyclohexanone.

28. (Currently Amended) The resist flow process according to claim 13, wherein said organic solvent is present in an amount ranging from 100wt% to 1000wt% ~~by weight~~ of the photoresist polymer.

29. (New) The resist flow process according to claim 23, wherein ~~said~~ step (a) further comprises the steps of:

(i) coating said photoresist composition on said substrate to form a photoresist film, wherein said substrate is a semiconductor device; and

(ii) producing said first photoresist pattern using a lithography process.

30. (New) The resist flow process according to claim 23, wherein said first and second photoresist pattern comprises a contact hole pattern.

31. (New) The resist flow process according to claim 13, wherein said resist flow process comprises heating to a temperature between Tg of the photoresist polymer and a decomposition temperature (T_d) where the polymer starts to be decomposed.

32. (New) The resist flow process according to claim 23, wherein said additive is present in an amount ranging from 1 wt% to 70 wt% of the photoresist polymer.

33. (New) The resist flow process according to claim 23, wherein said photoacid generator is selected from the group consisting of diphenyl iodide hexafluorophosphate, diphenyl iodide hexafluoroarsenate, diphenyl iodide hexafluoroantimonate, diphenyl p-methoxyphenyl triflate, diphenyl p-toluenyl triflate, diphenyl p-isobutylphenyl triflate, diphenyl p-tert-butylphenyl triflate, triphenylsulfonium hexafluororphosphate, triphenylsulfonium hexafluoroarsenate, triphenylsulfonium hexafluoroantimonate, triphenylsulfonium triflate, dibutylnaphthylsulfonium triflate, and mixtures thereof.

34. (New) The resist flow process according to claim 23, wherein said photoacid generator is present in an amount ranging from 0.01 wt% to 10 wt% of the photoresist polymer.

35. (New) The resist flow process according to claim 23, wherein said organic solvent is selected from the group consisting of propyleneglycol methyl ether acetate, ethyl lactate, methyl 3-methoxypropionate, ethyl 3-ethoxypropionate and cyclohexanone.

36. (Currently Amended) The resist flow process according to claim 23, wherein said organic solvent is present in an amount ranging from 100 wt% to 1000 wt% of the photoresist polymer.